

DCR2180H85

Phase Control Thyristor

DS6065-1 April 2011 (LN28305)

FEATURES

- Double Side Cooling
- High Surge Capability

KEY PARAMETERS

V _{DRM}	8500 V
I _{T(AV)}	2180 A
ITSM	40000 A
dV/dt*	2000 V/µs
dl/dt	100 A/µs

APPLICATIONS

- High Power Drives
- High Voltage Power Supplies
- Static Switches

VOLTAGE RATINGS

Part and Ordering Number	Repetitive Peak Voltages V _{DSM} and V _{RSM} V	Conditions
DCR2180H85 DCR2180H80 DCR2180H75 DCR2180H70	8500 8000 7500 7000	$\begin{array}{l} T_{vj} = -40^{\circ}C \ to \ 90^{\circ}C, \\ I_{DRM} = I_{RRM} = 700 \text{mA}, \\ V_{DRM}, \ V_{RRM} \ t_p = 10 \text{ms}, \\ V_{DRM} \& \ V_{RRM} = \\ V_{DSM} \& \ V_{RSM} - 500 V \\ respectively \end{array}$

Lower voltage grades available.

ORDERING INFORMATION

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

DCR2180H85

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

* Higher dV/dt selections available

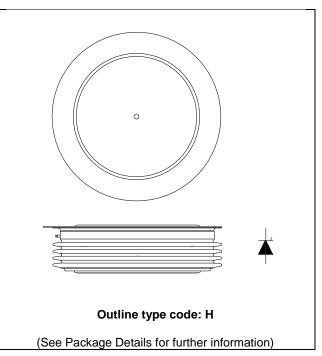


Fig. 1 Package outline

www.dynexsemi.com



CURRENT RATINGS

 $T_{case} = 60^{\circ}C$ unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
Double Si	de Cooled			
I _{T(AV)}	Mean on-state current	Half wave resistive load	2180	А
I _{T(RMS)}	RMS value	-	3420	А
Ι _Τ	Continuous (direct) on-state current	-	3080	А

SURGE RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
I _{TSM}	Surge (non-repetitive) on-state current	10ms half sine, T _{case} = 90°C	40.0	kA
l ² t	I ² t for fusing	V _R = 0	8.00	MA ² s

THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Conditions		Min.	Max.	Units
R _{th(j-c)}	Thermal resistance – junction to case	Double side cooled	DC	-	0.004	°C/W
R _{th(c-h)}	Thermal resistance – case to heatsink	Double side cooled	DC	-	0.0008	°C/W
T_{vj}	Virtual junction temperature	Blocking V _{DRM} / _{VRRM}		-40	90	°C
T _{stg}	Storage temperature range			-40	140	°C
Fm	Clamping force			110	130	kN



DYNAMIC CHARACTERISTICS

Symbol	Parameter	Test Conditions		Min.	Max.	Units
I _{RRM} /I _{DRM}	Peak reverse and off-state current	At V_{RRM}/V_{DRM} , $T_{case} = 90^{\circ}C$	At V _{RRM} /V _{DRM} , T _{case} = 90°C		700	mA
dV/dt	Max. linear rate of rise of off-state voltage	To 67% V_{DRM} , $T_j = 90^{\circ}C$, gat	te open	2000	-	V/µs
dl/dt	Rate of rise of on-state current	From 67% V _{DRM} to 4000A	Repetitive 50Hz	-	200	A/µs
		Gate source 30V, 10Ω ,	Non-repetitive	-	1000	A/µs
		$t_r < 0.5 \mu s, \ T_j = 90^\circ C$				
V _T	On-state voltage	I _T = 1500A, T _{case} = 90°C			1.90	V
V _{T(TO)}	Threshold voltage	T _{case} = 90°C		-	1.30	V
r _T	On-state slope resistance	T _{case} = 90°C		-	0.40	mΩ
t _{gd}	Delay time	$V_D = 67\% V_{DRM}$, gate source 30V, 10 Ω		-	3.0	μs
		$t_r = 0.5 \mu s, T_j = 25^{\circ}C$				
tq	Turn-off time	$T_j = 90^{\circ}C, V_R = 100V, dI/dt = 1.5A/\mu s,$		-	1200	μs
		$dV_{DR}/dt = 20V/\mu s$ linear to 67% V_{DRM}				
Qs	Stored charge	$I_T = 2500A, tp = 700us, T_j = 90^{\circ}C,$		-	6500	μC
		dl/dt =1.5A/µs,				
١L	Latching current	$T_j = 25^{\circ}C,$		-	1	А
I _H	Holding current	$T_j = 25^{\circ}C,$		-	200	mA

GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
V _{GT}	Gate trigger voltage	$V_{DRM} = 5V, T_{case} = 25^{\circ}C$	2.6	V
V_{GD}	Gate non-trigger voltage	At 40% V _{DRM} , T _{case} = 90°C	TBD	V
I _{GT}	Gate trigger current	$V_{DRM} = 5V, T_{case} = 25^{\circ}C$	400	mA
I _{GD}	Gate non-trigger current	At 40% V _{DRM,} T _{case} = 90°C	TBD	mA



CURVES

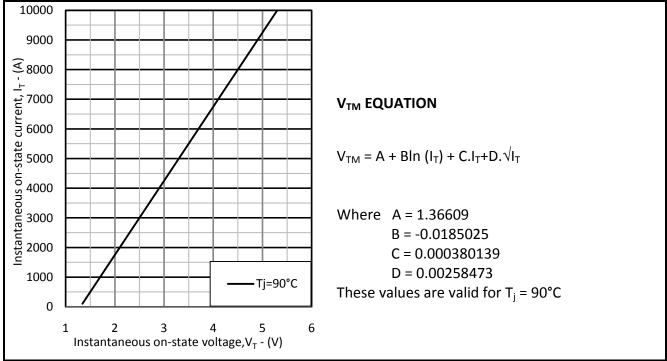


Fig.2 Maximum & minimum on-state characteristics

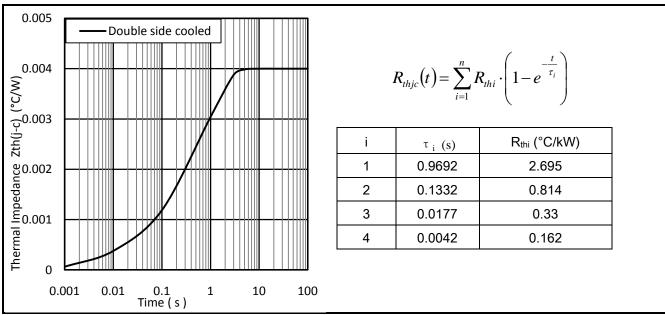
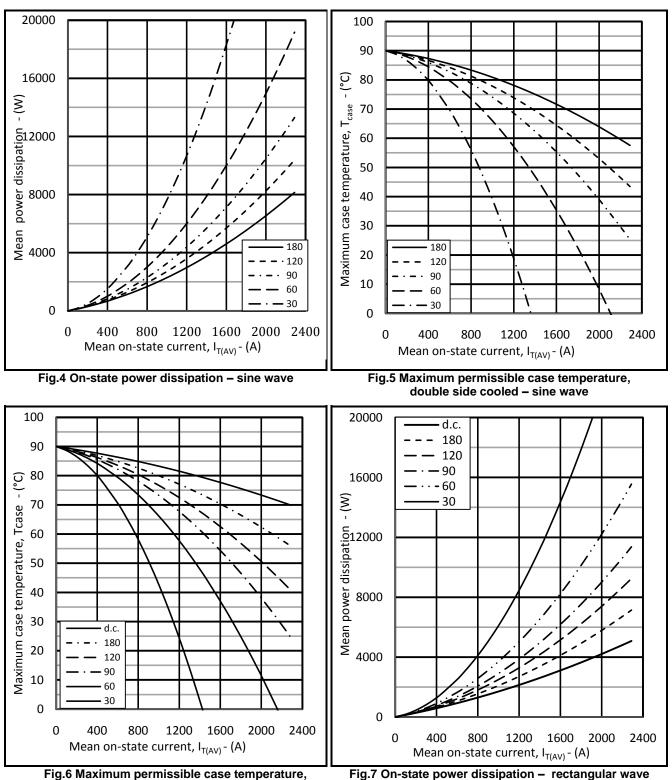


Fig.3 Maximum (limit) transient thermal impedance – junction to case (°C/W)





double side cooled - rectangular wave





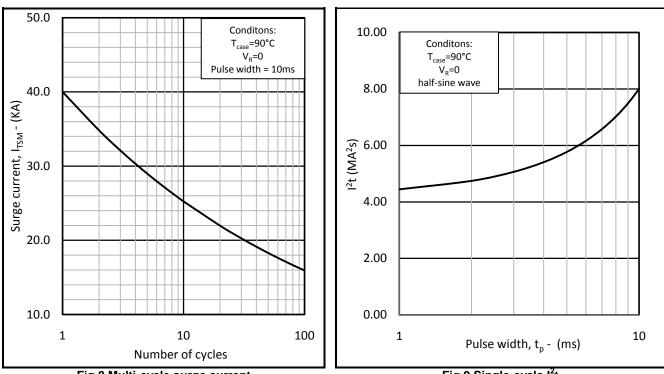


Fig.8 Multi-cycle surge current

Fig.9 Single-cycle I²t

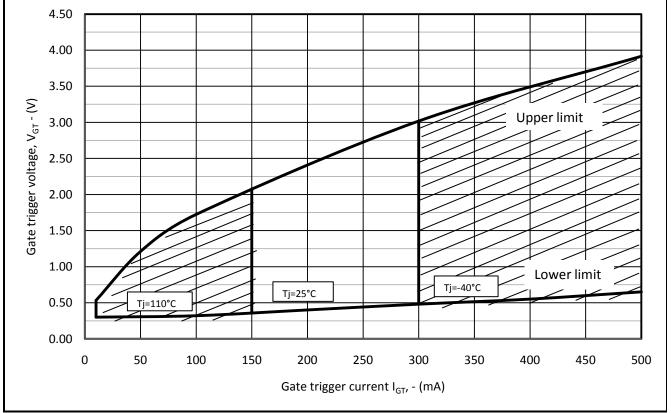


Fig.10 Gate characteristics



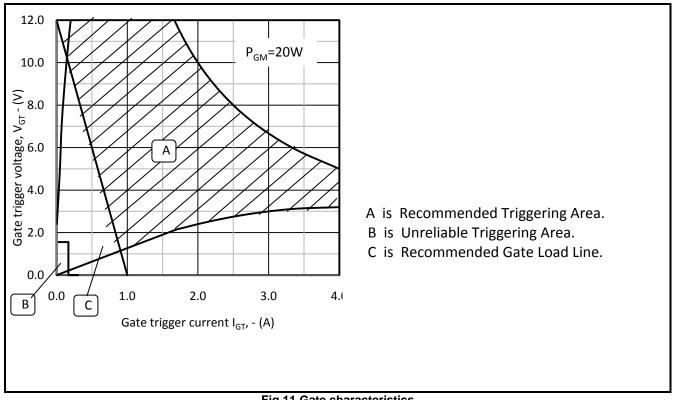


Fig.11 Gate characteristics



PACKAGE DETAILS

For further package information, please contact Customer Services. All dimensions in mm, unless stated otherwise. DO NOT SCALE.

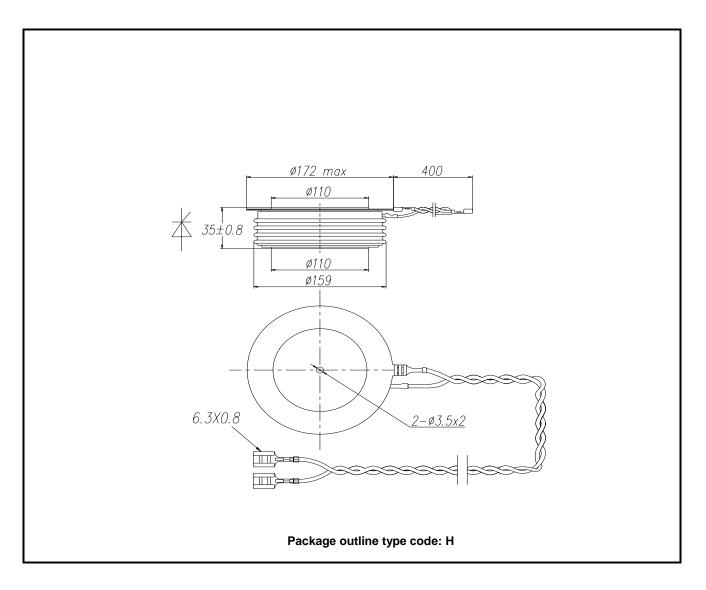


Fig.12 Package outline



SEMICONDUCTOR

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